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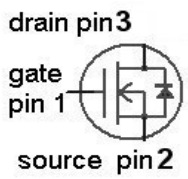
SIPMOS® Small-Signal-Transistor

Features

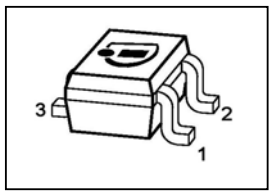
- N-channel
- Enhancement mode
- Logic level
- d*v*/d*t* rated
- Pb-free lead-plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	60	V
$R_{DS(on),max}$	3.5	Ω
I_D	0.28	A



PG-SOT-323



Type	Package	Tape and Reel	Marking
BSS138W	PG-SOT-323	H6327: 3000 / H6433: 10000	SWs
BSS138W	PG-SOT-323	H6433: 10000	SWs

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	0.28	A
		T_A=70 °C	0.22	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	1.12	
Reverse diode d*v*/d*t*	d*v*/d*t*	I_D=0.28 A, V_{DS}=48 V, d*i*/d*t*=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±20	V
ESD class (JESD22-A114-HBM)			0 (<250V)	
Power dissipation	P_{tot}	T_A=25 °C	0.50	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

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Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - minimal footprint	R_{thJA}		-	-	250	K/W
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}= 0 V, I_D=250 µA	60	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=26 µA	0.6	1.0	1.4	
Drain-source leakage current	$I_{D (off)}$	V_{DS}=60 V, V_{GS}=0 V, T_j=25 °C	-	-	0.1	µA
		V_{DS}=60 V, V_{GS}=0 V, T_j=150 °C	-	-	5	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	10	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5 V, I_D=0.03 A	-	3	4.0	Ω
		V_{GS}=4.5 V, I_D=0.16 A	-	3.2	6	
		V_{GS}=10 V, I_D=0.2 A	-	2.1	3.5	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=0.22 A	0.12	0.23	-	S

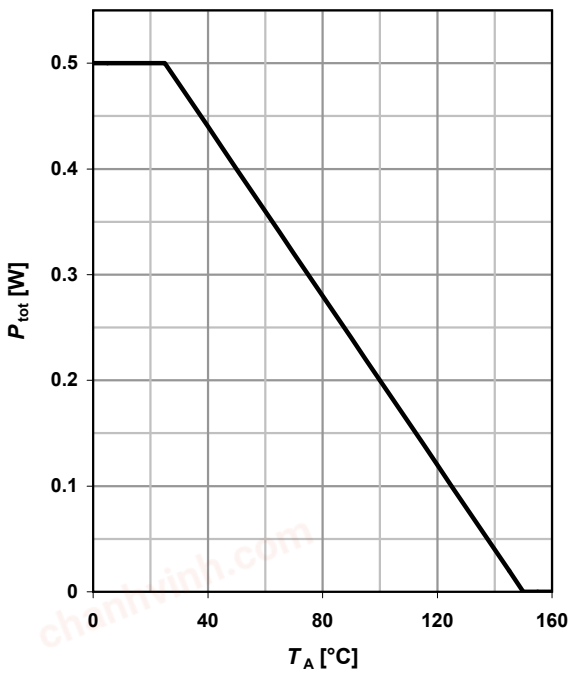
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Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=25 V, f=1 MHz	-	32	43	pF
Output capacitance	C_{oss}		-	7.2	10	
Reverse transfer capacitance	C_{rss}		-	2.8	4.2	
Turn-on delay time	$t_{d(on)}$	V_{DD}=30 V, V_{GS}=10 V, I_D=0.2 A, R_G=6 Ω	-	2.2	3.3	ns
Rise time	t_r		-	3.0	4.5	
Turn-off delay time	$t_{d(off)}$		-	6.7	10	
Fall time	t_f		-	8.2	12	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=48 V, I_D=0.2 A, V_{GS}=0 to 10 V	-	0.10	0.13	nC
Gate to drain charge	Q_{gd}		-	0.3	0.4	
Gate charge total	Q_g		-	1.0	1.5	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	0.28	A
Diode pulse current	$I_{S,pulse}$		-	-	1.12	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=0.28 A, T_j=25 °C	-	0.85	1.2	V
Reverse recovery time	t_{rr}	V_R=30 V, I_F=0.28 A, di_F/dt=100 A/µs	-	8.3	12.4	ns
Reverse recovery charge	Q_{rr}		-	3.3	5	nC

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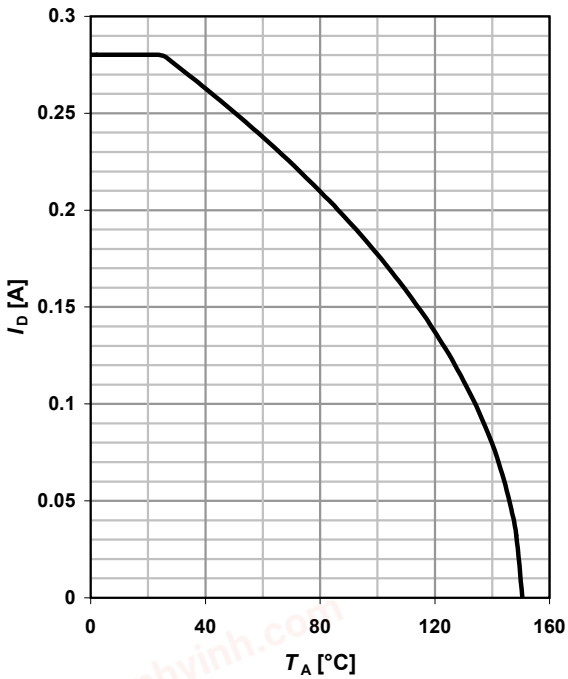
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

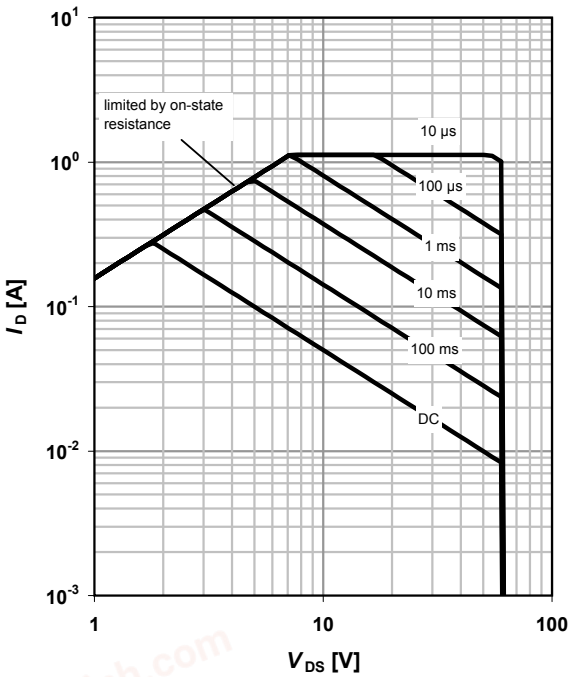
$I_D=f(T_A)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_A=25$ °C; $D=0$

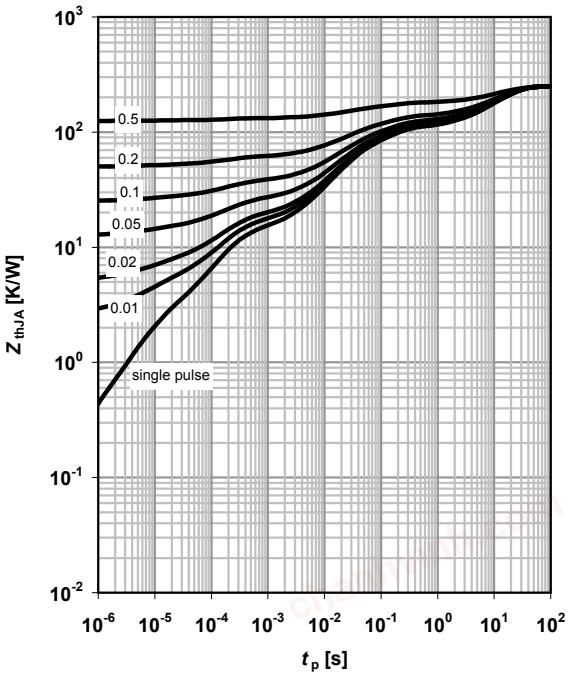
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

parameter: $D=t_p/T$

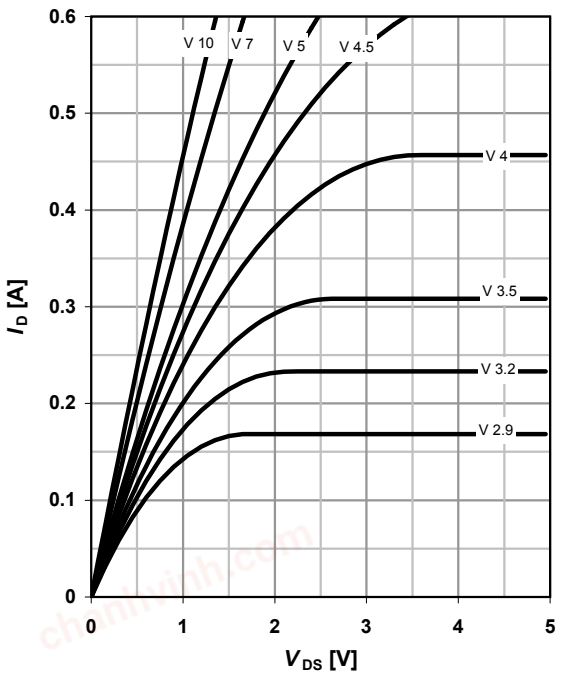


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5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

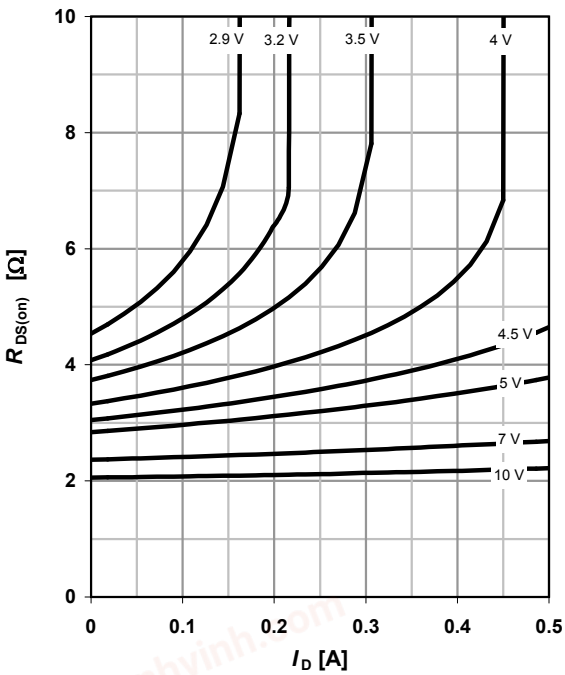
parameter: V_{GS}



6 Typ. drain-source on resistance

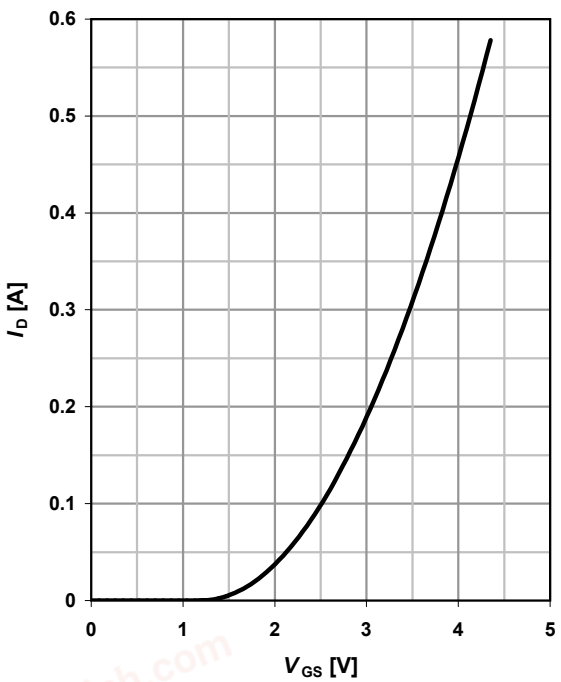
$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}



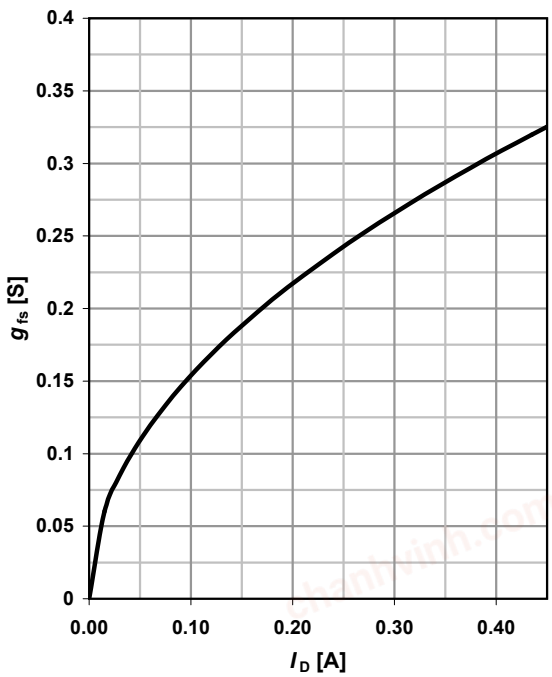
7 Typ. transfer characteristics

I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$



8 Typ. forward transconductance

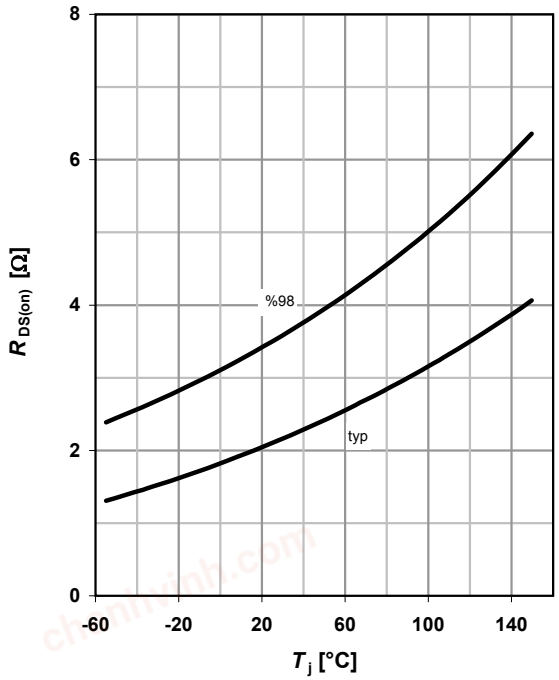
g_{fs}=f(I_D); T_j=25 °C



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9 Drain-source on-state resistance

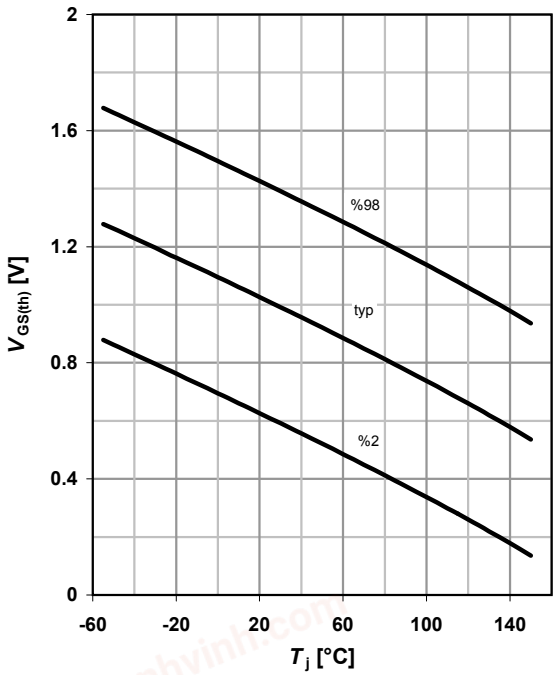
$R_{DS(on)}$=f(T_j); I_D=0.2 A; V_{GS}=10 V



10 Typ. gate threshold voltage

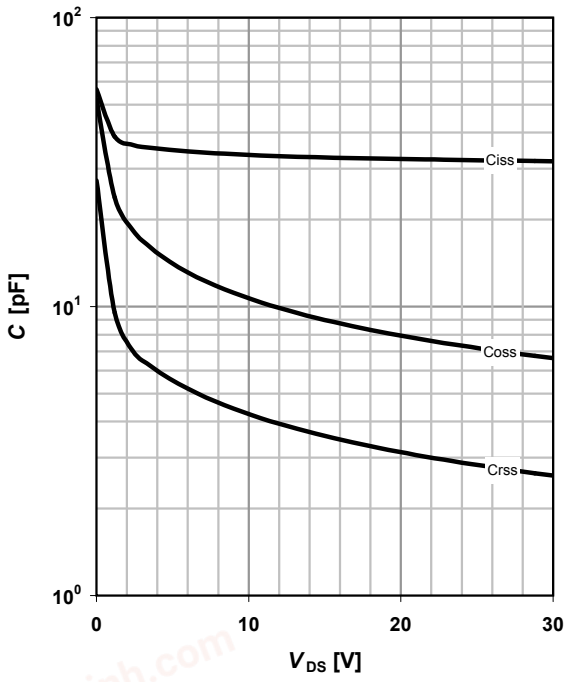
$V_{GS(th)}$=f(T_j); V_{DS}=V_{GS}; I_D=26 µA

parameter: I_D



11 Typ. capacitances

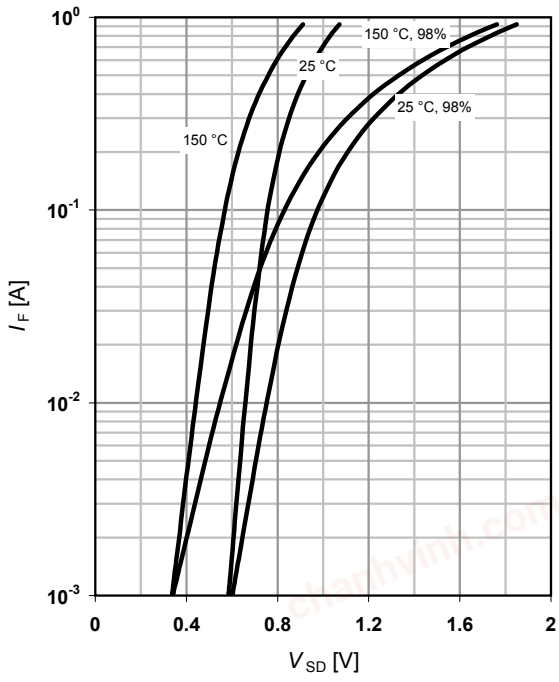
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz; T_j=25°C



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

parameter: T_j

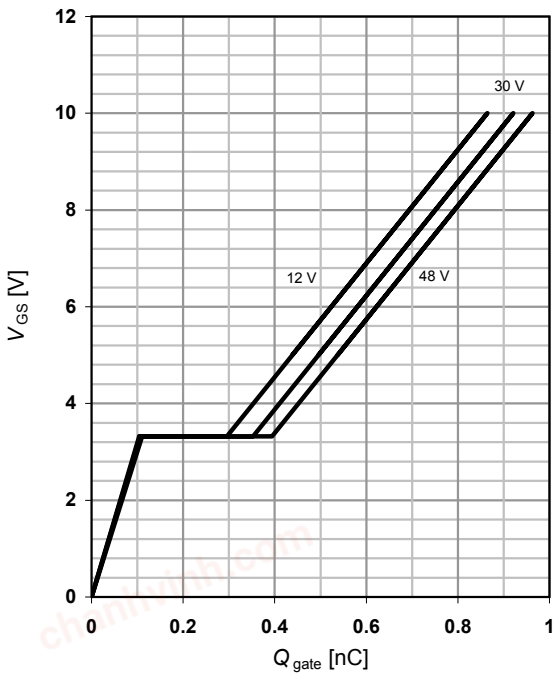


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13 Typ. gate charge

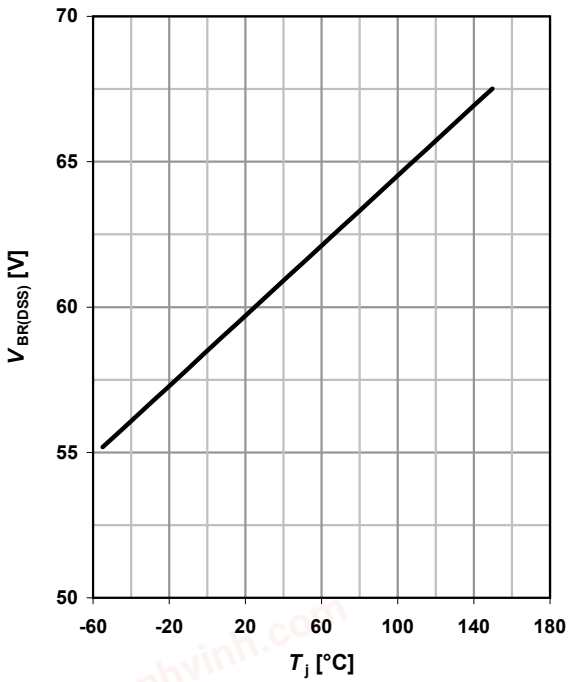
V_{GS}=f(Q_{gate}); I_D=0.2 A pulsed

parameter: V_{DD}



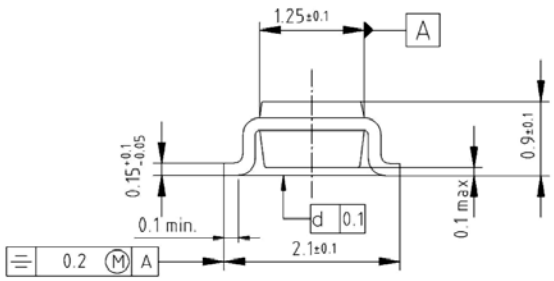
14 Drain-source breakdown voltage

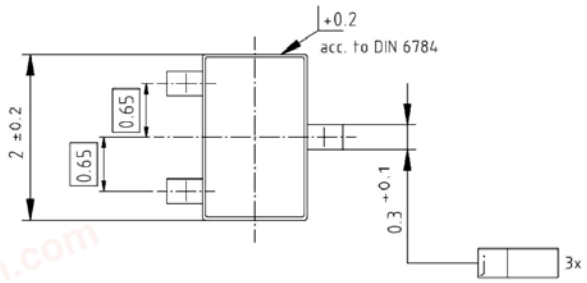
$V_{BR(DSS)}$=f(T_j); I_D=250 µA



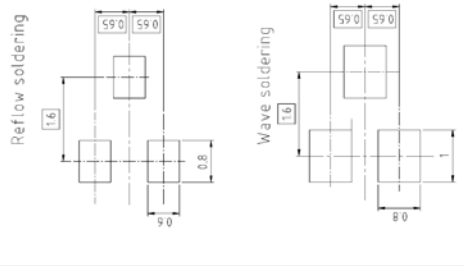
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Package Outline:

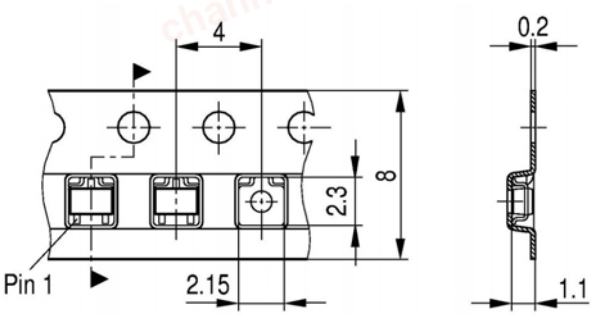




Footprint:



Packaging:



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